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Kind regards,

Team Nexperia

74HC193; 74HCT193

Presetable synchronous 4-bit binary up/down counter

Rev. 5 — 29 January 2016

Product data sheet

1. General description

The 74HC193; 74HCT193 is a 4-bit synchronous binary up/down counter. Separate up/down clocks, CPU and CPD respectively, simplify operation. The outputs change state synchronously with the LOW-to-HIGH transition of either clock input. If the CPU clock is pulsed while CPD is held HIGH, the device will count up. If the CPD clock is pulsed while CPU is held HIGH, the device will count down. Only one clock input can be held HIGH at any time to guarantee predictable behavior. The device can be cleared at any time by the asynchronous master reset input ($\overline{\text{MR}}$); it may also be loaded in parallel by activating the asynchronous parallel load input ($\overline{\text{PL}}$). The terminal count up ($\overline{\text{TCU}}$) and terminal count down ($\overline{\text{TCD}}$) outputs are normally HIGH. When the circuit has reached the maximum count state of 15, the next HIGH-to-LOW transition of CPU will cause $\overline{\text{TCU}}$ to go LOW. $\overline{\text{TCU}}$ will stay LOW until CPU goes HIGH again, duplicating the count up clock. Likewise, the $\overline{\text{TCD}}$ output will go LOW when the circuit is in the zero state and the CPD goes LOW. The terminal count outputs can be used as the clock input signals to the next higher order circuit in a multistage counter, since they duplicate the clock waveforms. Multistage counters will not be fully synchronous, since there is a slight delay time difference added for each stage that is added. The counter may be preset by the asynchronous parallel load capability of the circuit. Information present on the parallel data inputs (D0 to D3) is loaded into the counter and appears on the outputs ($\overline{\text{Q0}}$ to Q3) regardless of the conditions of the clock inputs when the parallel load ($\overline{\text{PL}}$) input is LOW. A HIGH level on the master reset ($\overline{\text{MR}}$) input will disable the parallel load gates, override both clock inputs and set all outputs (Q0 to Q3) LOW. If one of the clock inputs is LOW during and after a reset or load operation, the next LOW-to-HIGH transition of that clock will be interpreted as a legitimate signal and will be counted. Inputs include clamp diodes. This enables the use of current limiting resistors to interface inputs to voltages in excess of V_{CC} .

2. Features and benefits

- Input levels:
 - ◆ For 74HC193: CMOS level
 - ◆ For 74HCT193: TTL level
- Synchronous reversible 4-bit binary counting
- Asynchronous parallel load
- Asynchronous reset
- Expandable without external logic
- Complies with JEDEC standard no. 7A
- ESD protection:
 - ◆ HBM JESD22-A114F exceeds 2000 V
 - ◆ MM JESD22-A115-A exceeds 200 V.



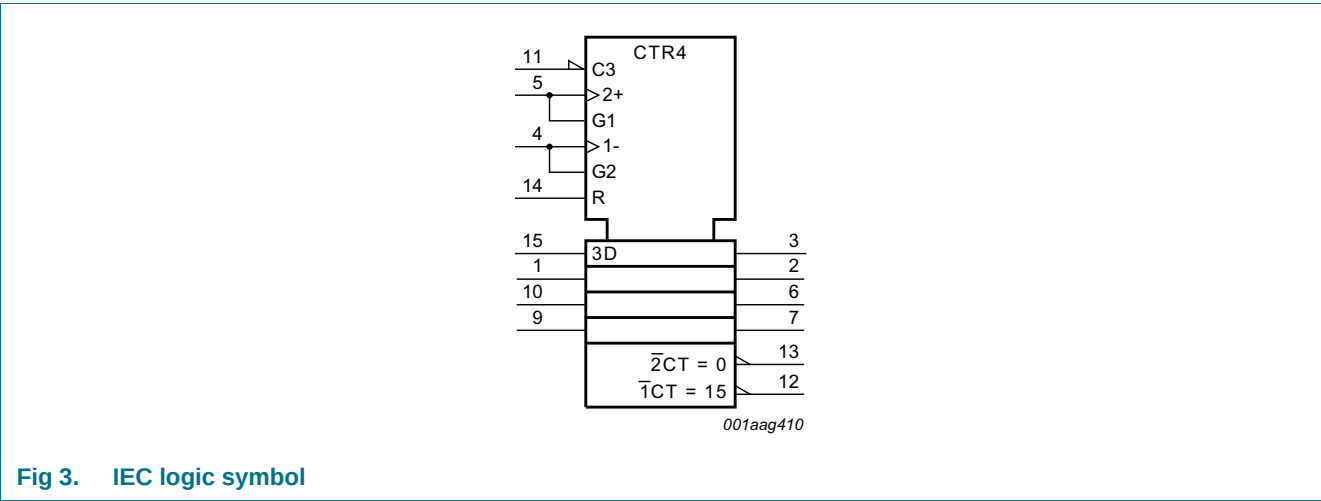
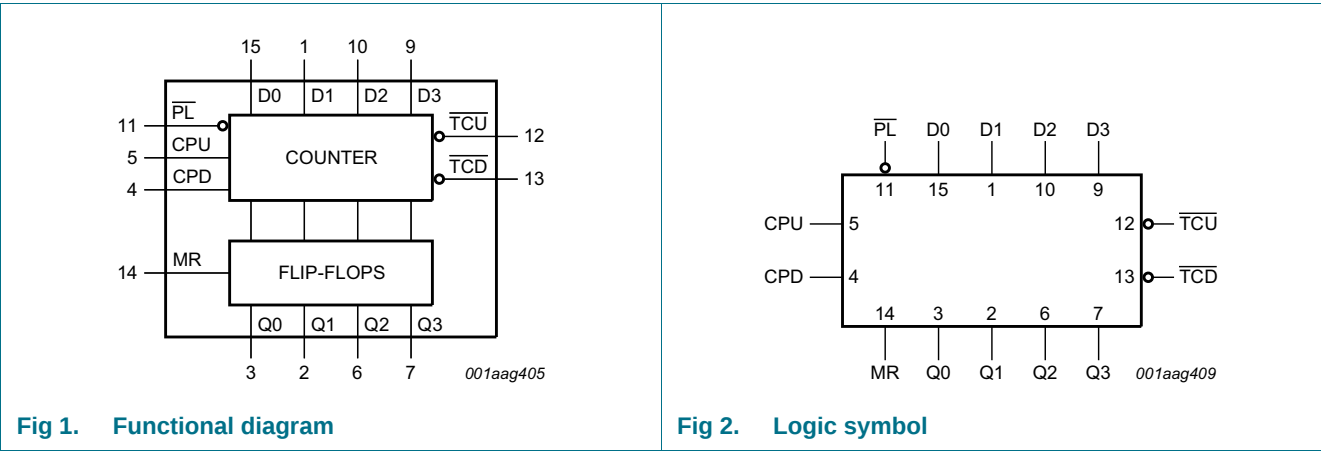
- Multiple package options
- Specified from -40 °C to +85 °C and -40 °C to +125 °C.

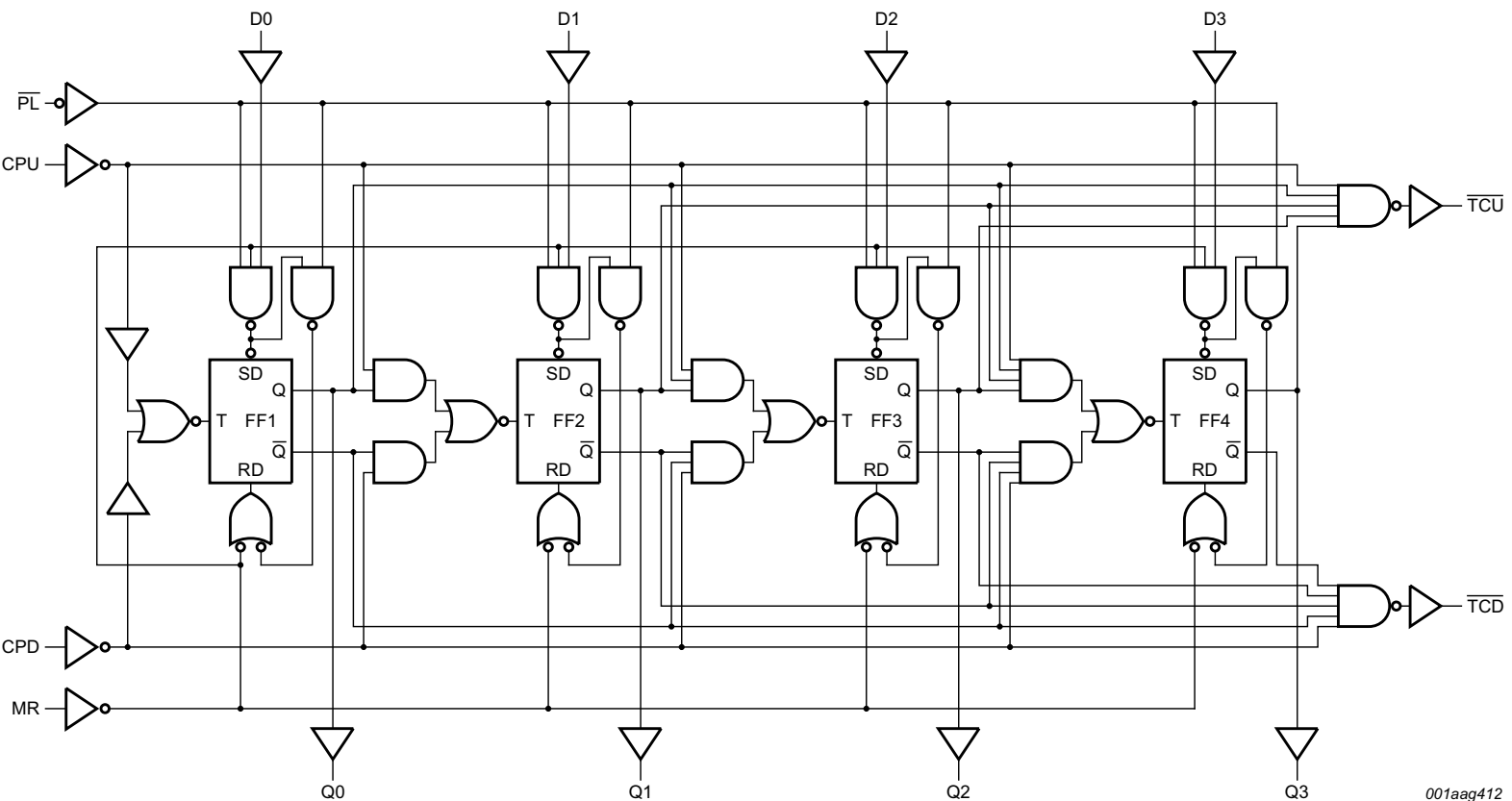
3. Ordering information

Table 1. Ordering information

Type number	Package			
	Temperature range	Name	Description	Version
74HC193D	-40 °C to +125 °C	SO16	plastic small outline package; 16 leads; body width 3.9 mm	SOT109-1
74HCT193D				
74HC193DB	-40 °C to +125 °C	SSOP16	plastic shrink small outline package; 16 leads; body width 5.3 mm	SOT338-1
74HCT193DB				
74HC193PW	-40 °C to +125 °C	TSSOP16	plastic thin shrink small outline package; 16 leads; body width 4.4 mm	SOT403-1
74HCT193PW				

4. Functional diagram



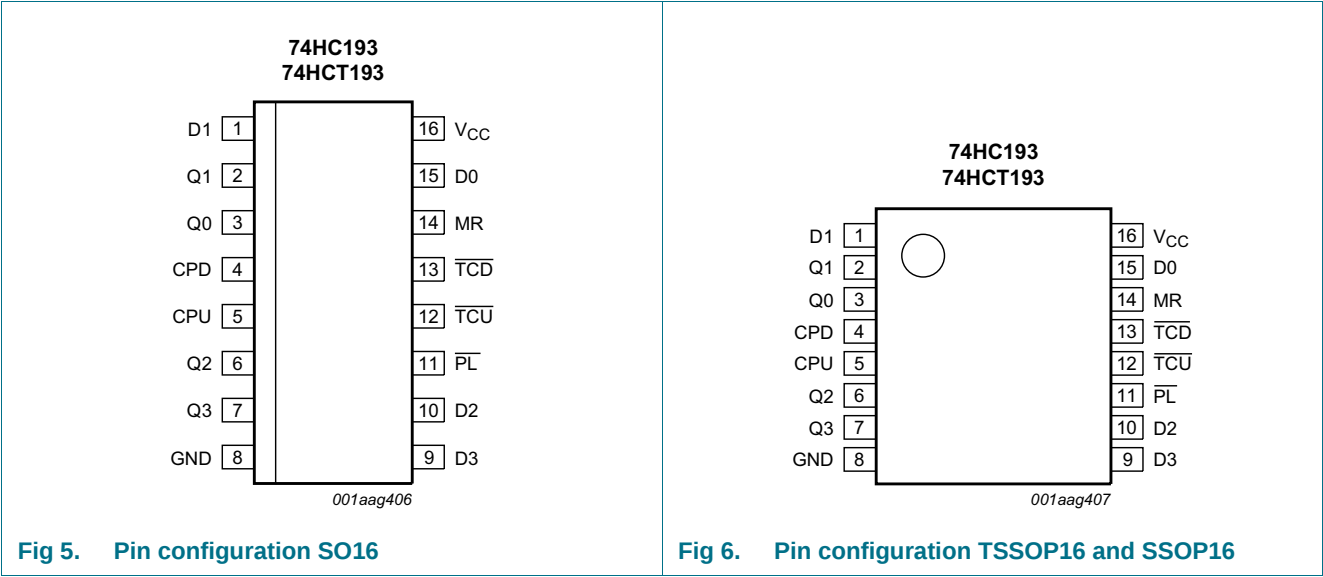


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Fig 4. Logic diagram

5. Pinning information

5.1 Pinning



5.2 Pin description

Table 2. Pin description

Symbol	Pin	Description
D0	15	data input 0
D1	1	data input 1
D2	10	data input 2
D3	9	data input 3
Q0	3	flip-flop output 0
Q1	2	flip-flop output 1
Q2	6	flip-flop output 2
Q3	7	flip-flop output 3
CPD	4	count down clock input ^[1]
CPU	5	count up clock input ^[1]
GND	8	ground (0 V)
$\overline{\text{PL}}$	11	asynchronous parallel load input (active LOW)
$\overline{\text{TCU}}$	12	terminal count up (carry) output (active LOW)
$\overline{\text{TCD}}$	13	terminal count down (borrow) output (active LOW)
MR	14	asynchronous master reset input (active HIGH)
V _{CC}	16	supply voltage

[1] LOW-to-HIGH, edge triggered.

6. Functional description

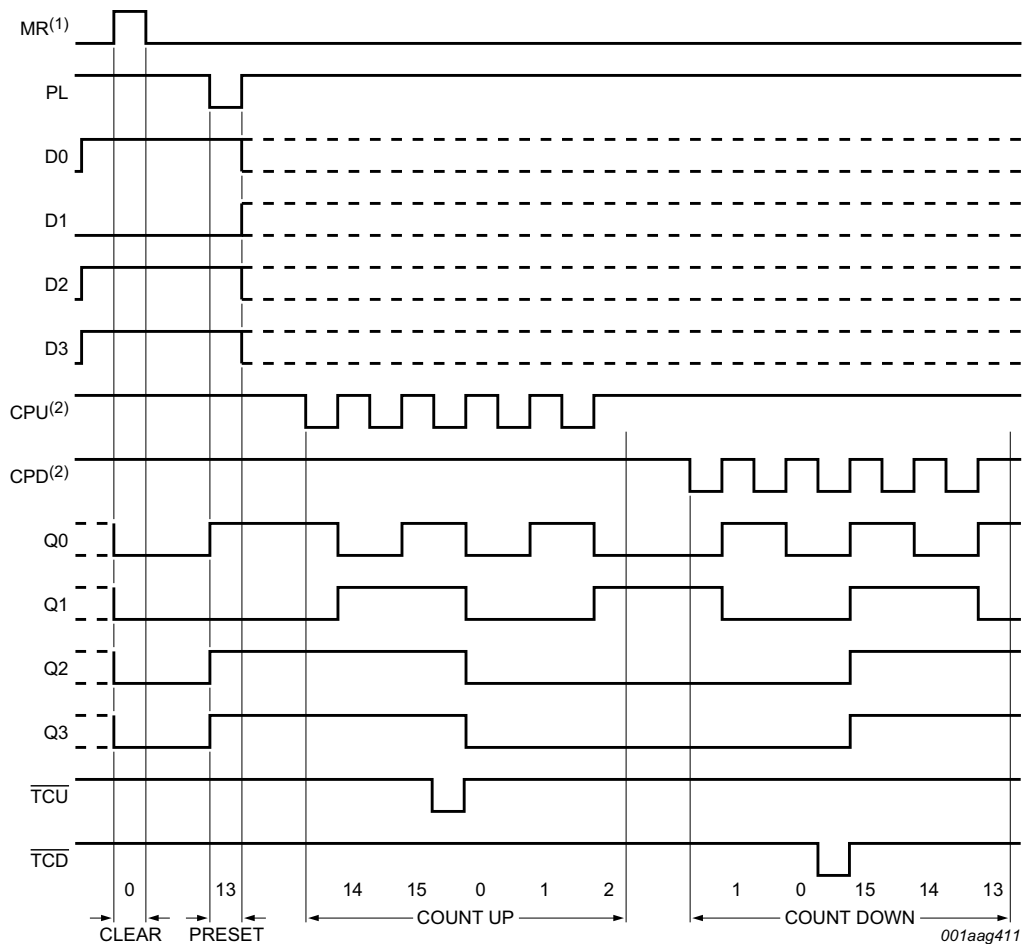
Table 3. Function table^[1]

Operating mode	Inputs								Outputs					
	MR	PL	CPU	CPD	D0	D1	D2	D3	Q0	Q1	Q2	Q3	TCU	TCD
Reset (clear)	H	X	X	L	X	X	X	X	L	L	L	L	H	L
	H	X	X	H	X	X	X	X	L	L	L	L	H	H
Parallel load	L	L	X	L	L	L	L	L	L	L	L	L	H	L
	L	L	X	H	L	L	L	L	L	L	L	L	H	H
	L	L	L	X	H	H	H	H	H	H	H	H	L	H
	L	L	H	X	H	H	H	H	H	H	H	H	H	H
Count up	L	H	↑	H	X	X	X	X	count up				H ^[2]	H
Count down	L	H	H	↑	X	X	X	X	count down				H	H ^[3]

- [1] H = HIGH voltage level
 L = LOW voltage level
 X = don't care
 ↑ = LOW-to-HIGH clock transition.

[2] $\overline{\text{TCU}}$ = CPU at terminal count up (HHHH)

[3] $\overline{\text{TCD}}$ = CPD at terminal count down (LLLL).



- (1) Clear overrides load, data and count inputs.
- (2) When counting up, the count down clock input (CPD) must be HIGH, when counting down the count up clock input (CPU) must be HIGH.

Sequence

Clear (reset outputs to zero);

load (preset) to binary thirteen;

count up to fourteen, fifteen, terminal count up, zero, one and two;

count down to one, zero, terminal count down, fifteen, fourteen and thirteen.

Fig 7. Typical clear, load and count sequence

7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CC}	supply voltage		-0.5	+7.0	V
I_{IK}	input clamping current	$V_I < -0.5\text{ V}$ or $V_I > V_{CC} + 0.5\text{ V}$ [1]	-	± 20	mA
I_{OK}	output clamping current	$V_O < -0.5\text{ V}$ or $V_O > V_{CC} + 0.5\text{ V}$ [1]	-	± 20	mA
I_O	output current	$V_O = -0.5\text{ V}$ to $V_{CC} + 0.5\text{ V}$	-	± 25	mA
I_{CC}	supply current		-	50	mA
I_{GND}	ground current		-	-50	mA
T_{stg}	storage temperature		-65	+150	°C
P_{tot}	total power dissipation	SO16 package [2]	-	500	mW
		SSOP16 package [2]	-	500	mW
		TSSOP16 package [2]	-	500	mW

[1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

[2] For SO16 packages: above 70 °C the value of P_{tot} derates linearly at 8 mW/K.

For SSOP16 and TSSOP16 packages: above 60 °C the value of P_{tot} derates linearly at 5.5 mW/K.

8. Recommended operating conditions

Table 5. Recommended operating conditions

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
74HC193						
V _{CC}	supply voltage		2.0	5.0	6.0	V
V _I	input voltage		0	-	V _{CC}	V
V _O	output voltage		0	-	V _{CC}	V
T _{amb}	ambient temperature		−40	+25	+125	°C
Δt/ΔV	input transition rise and fall rate	V _{CC} = 2.0 V	-	-	625	ns/V
		V _{CC} = 4.5 V	-	1.67	139	ns/V
		V _{CC} = 6.0 V	-	-	83	ns/V
74HCT193						
V _{CC}	supply voltage		4.5	5.0	5.5	V
V _I	input voltage		0	-	V _{CC}	V
V _O	output voltage		0	-	V _{CC}	V
T _{amb}	ambient temperature		−40	+25	+125	°C
Δt/ΔV	input transition rise and fall rate	V _{CC} = 4.5 V	-	1.67	139	ns/V

9. Static characteristics

Table 6. Static characteristics type 74HC193

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
T_{amb} = 25 °C						
V _{IH}	HIGH-level input voltage	V _{CC} = 2.0 V	1.5	1.2	-	V
		V _{CC} = 4.5 V	3.15	2.4	-	V
		V _{CC} = 6.0 V	4.2	3.2	-	V
V _{IL}	LOW-level input voltage	V _{CC} = 2.0 V	-	0.8	0.5	V
		V _{CC} = 4.5 V	-	2.1	1.35	V
		V _{CC} = 6.0 V	-	2.8	1.8	V
V _{OH}	HIGH-level output voltage	V _I = V _{IH} or V _{IL}	-	-	-	
		I _O = -20 µA; V _{CC} = 2.0 V	1.9	2.0	-	V
		I _O = -20 µA; V _{CC} = 4.5 V	4.4	4.5	-	V
		I _O = -20 µA; V _{CC} = 6.0 V	5.9	6.0	-	V
		I _O = -4.0 mA; V _{CC} = 4.5 V	3.98	4.32	-	V
		I _O = -5.2 mA; V _{CC} = 6.0 V	5.48	5.81	-	V
V _{OL}	LOW-level output voltage	V _I = V _{IH} or V _{IL}				
		I _O = 20 µA; V _{CC} = 2.0 V	-	0	0.1	V
		I _O = 20 µA; V _{CC} = 4.5 V	-	0	0.1	V
		I _O = 20 µA; V _{CC} = 6.0 V	-	0	0.1	V
		I _O = 4.0 mA; V _{CC} = 4.5 V	-	0.15	0.26	V
		I _O = 5.2 mA; V _{CC} = 6.0 V	-	0.16	0.26	V
I _I	input leakage current	V _I = V _{CC} or GND; V _{CC} = 6.0 V	-	-	±0.1	µA
I _{CC}	supply current	V _I = V _{CC} or GND; I _O = 0 A; V _{CC} = 6.0 V	-	-	8.0	µA
C _i	input capacitance		-	3.5	-	pF
T_{amb} = -40 °C to +85 °C						
V _{IH}	HIGH-level input voltage	V _{CC} = 2.0 V	1.5	-	-	V
		V _{CC} = 4.5 V	3.15	-	-	V
		V _{CC} = 6.0 V	4.2	-	-	V
V _{IL}	LOW-level input voltage	V _{CC} = 2.0 V	-	-	0.5	V
		V _{CC} = 4.5 V	-	-	1.35	V
		V _{CC} = 6.0 V	-	-	1.8	V
V _{OH}	HIGH-level output voltage	V _I = V _{IH} or V _{IL}				
		I _O = -20 µA; V _{CC} = 2.0 V	1.9	-	-	V
		I _O = -20 µA; V _{CC} = 4.5 V	4.4	-	-	V
		I _O = -20 µA; V _{CC} = 6.0 V	5.9	-	-	V
		I _O = -4.0 mA; V _{CC} = 4.5 V	3.84	-	-	V
		I _O = -5.2 mA; V _{CC} = 6.0 V	5.34	-	-	V

Table 6. Static characteristics type 74HC193 ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V _{OL}	LOW-level output voltage	V _I = V _{IH} or V _{IL}				
		I _O = 20 µA; V _{CC} = 2.0 V	-	-	0.1	V
		I _O = 20 µA; V _{CC} = 4.5 V	-	-	0.1	V
		I _O = 20 µA; V _{CC} = 6.0 V	-	-	0.1	V
		I _O = 4.0 mA; V _{CC} = 4.5 V	-	-	0.33	V
		I _O = 5.2 mA; V _{CC} = 6.0 V	-	-	0.33	V
I _I	input leakage current	V _I = V _{CC} or GND; V _{CC} = 6.0 V	-	-	±1.0	µA
I _{CC}	supply current	V _I = V _{CC} or GND; I _O = 0 A; V _{CC} = 6.0 V	-	-	80	µA
T _{amb} = -40 °C to +125 °C						
V _{IH}	HIGH-level input voltage	V _{CC} = 2.0 V	1.5	-	-	V
		V _{CC} = 4.5 V	3.15	-	-	V
		V _{CC} = 6.0 V	4.2	-	-	V
V _{IL}	LOW-level input voltage	V _{CC} = 2.0 V	-	-	0.5	V
		V _{CC} = 4.5 V	-	-	1.35	V
		V _{CC} = 6.0 V	-	-	1.8	V
V _{OH}	HIGH-level output voltage	V _I = V _{IH} or V _{IL}				
		I _O = -20 µA; V _{CC} = 2.0 V	1.9	-	-	V
		I _O = -20 µA; V _{CC} = 4.5 V	4.4	-	-	V
		I _O = -20 µA; V _{CC} = 6.0 V	5.9	-	-	V
		I _O = -4.0 mA; V _{CC} = 4.5 V	3.7	-	-	V
		I _O = -5.2 mA; V _{CC} = 6.0 V	5.2	-	-	V
V _{OL}	LOW-level output voltage	V _I = V _{IH} or V _{IL}				
		I _O = 20 µA; V _{CC} = 2.0 V	-	-	0.1	V
		I _O = 20 µA; V _{CC} = 4.5 V	-	-	0.1	V
		I _O = 20 µA; V _{CC} = 6.0 V	-	-	0.1	V
		I _O = 4.0 mA; V _{CC} = 4.5 V	-	-	0.4	V
		I _O = 5.2 mA; V _{CC} = 6.0 V	-	-	0.4	V
I _I	input leakage current	V _I = V _{CC} or GND; V _{CC} = 6.0 V	-	-	±1.0	µA
I _{CC}	supply current	V _I = V _{CC} or GND; I _O = 0 A; V _{CC} = 6.0 V	-	-	160	µA

Table 7. Static characteristics type 74HCT193

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
T _{amb} = 25 °C						
V _{IH}	HIGH-level input voltage	V _{CC} = 4.5 V to 5.5 V	2.0	1.6	-	V
V _{IL}	LOW-level input voltage	V _{CC} = 4.5 V to 5.5 V	-	1.2	0.8	V
V _{OH}	HIGH-level output voltage	V _I = V _{IH} or V _{IL} ; V _{CC} = 4.5 V				
		I _O = -20 µA	4.4	4.5	-	V
		I _O = -4.0 mA	3.98	4.32	-	V

Table 7. Static characteristics type 74HCT193 ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V _{OL}	LOW-level output voltage	V _I = V _{IH} or V _{IL} ; V _{CC} = 4.5 V				
		I _O = 20 μA	-	0	0.1	V
		I _O = 4.0 mA	-	0.15	0.26	V
I _I	input leakage current	V _I = V _{CC} or GND; V _{CC} = 5.5 V	-	-	±0.1	μA
I _{CC}	supply current	V _I = V _{CC} or GND; I _O = 0 A; V _{CC} = 5.5 V	-	-	8.0	μA
ΔI _{CC}	additional supply current	per input pin; V _I = V _{CC} – 2.1 V and other inputs at V _{CC} or GND; I _O = 0 A; V _{CC} = 4.5 V to 5.5 V				
		pin Dn	-	35	126	μA
		pins CPU, CPD	-	140	504	μA
		pin $\overline{\text{PL}}$	-	65	234	μA
		pin MR	-	105	378	μA
C _i	input capacitance		-	3.5	-	pF
T _{amb} = –40 °C to +85 °C						
V _{IH}	HIGH-level input voltage	V _{CC} = 4.5 V to 5.5 V	2.0	-	-	V
V _{IL}	LOW-level input voltage	V _{CC} = 4.5 V to 5.5 V	-	-	0.8	V
V _{OH}	HIGH-level output voltage	V _I = V _{IH} or V _{IL} ; V _{CC} = 4.5 V				
		I _O = –20 μA	4.4	-	-	V
		I _O = –4.0 mA	3.84	-	-	V
V _{OL}	LOW-level output voltage	V _I = V _{IH} or V _{IL} ; V _{CC} = 4.5 V				
		I _O = 20 μA	-	-	0.1	V
		I _O = 4.0 mA	-	-	0.33	V
I _I	input leakage current	V _I = V _{CC} or GND; V _{CC} = 5.5 V	-	-	±1.0	μA
I _{CC}	supply current	V _I = V _{CC} or GND; I _O = 0 A; V _{CC} = 5.5 V	-	-	80	μA
ΔI _{CC}	additional supply current	per input pin; V _I = V _{CC} – 2.1 V and other inputs at V _{CC} or GND; I _O = 0 A; V _{CC} = 4.5 V to 5.5 V				
		pin Dn	-	-	157.5	μA
		pins CPU, CPD	-	-	630	μA
		pin $\overline{\text{PL}}$	-	-	292.5	μA
		pin MR	-	-	472.5	μA
T _{amb} = –40 °C to +125 °C						
V _{IH}	HIGH-level input voltage	V _{CC} = 4.5 V to 5.5 V	2.0	-	-	V
V _{IL}	LOW-level input voltage	V _{CC} = 4.5 V to 5.5 V	-	-	0.8	V
V _{OH}	HIGH-level output voltage	V _I = V _{IH} or V _{IL} ; V _{CC} = 4.5 V				
		I _O = –20 μA	4.4	-	-	V
		I _O = –4.0 mA	3.7	-	-	V
V _{OL}	LOW-level output voltage	V _I = V _{IH} or V _{IL} ; V _{CC} = 4.5 V				
		I _O = 20 μA	-	-	0.1	V
		I _O = 4.0 mA	-	-	0.4	V

Table 7. Static characteristics type 74HCT193 ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
I_I	input leakage current	$V_I = V_{CC}$ or GND; $V_{CC} = 5.5$ V	-	-	± 1.0	μA
I_{CC}	supply current	$V_I = V_{CC}$ or GND; $I_O = 0$ A; $V_{CC} = 5.5$ V	-	-	160	μA
ΔI_{CC}	additional supply current	per input pin; $V_I = V_{CC} - 2.1$ V and other inputs at V_{CC} or GND; $I_O = 0$ A; $V_{CC} = 4.5$ V to 5.5 V				
		pin Dn	-	-	171.5	μA
		pins CPU, CPD	-	-	686	μA
		pin $\overline{PL}$	-	-	318.5	μA
		pin MR	-	-	514.5	μA

10. Dynamic characteristics

Table 8. Dynamic characteristics type 74HC193

Symbol	Parameter	Conditions	25 °C			–40 °C to +85 °C		–40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
t_{pd}	propagation delay	CPU, CPD to Qn; see Figure 8 ^[1]	-							
		$V_{CC} = 2.0\text{ V}$	-	63	215	-	270	-	325	ns
		$V_{CC} = 4.5\text{ V}$	-	23	43	-	54	-	65	ns
		$V_{CC} = 6.0\text{ V}$	-	18	37	-	46	-	55	ns
		CPU to TCU; see Figure 9								
		$V_{CC} = 2.0\text{ V}$	-	39	125	-	155	-	190	ns
		$V_{CC} = 4.5\text{ V}$	-	14	25	-	31	-	38	ns
		$V_{CC} = 6.0\text{ V}$	-	11	21	-	26	-	32	ns
		CPD to TCD; see Figure 9								
		$V_{CC} = 2.0\text{ V}$	-	39	125	-	155	-	190	ns
		$V_{CC} = 4.5\text{ V}$	-	14	25	-	31	-	38	ns
		$V_{CC} = 6.0\text{ V}$	-	11	21	-	26	-	32	ns
		PL to Qn; see Figure 10								
		$V_{CC} = 2.0\text{ V}$	-	69	220	-	275	-	330	ns
		$V_{CC} = 4.5\text{ V}$	-	25	44	-	55	-	66	ns
		$V_{CC} = 6.0\text{ V}$	-	20	37	-	47	-	56	ns
		MR to Qn; see Figure 11								
		$V_{CC} = 2.0\text{ V}$	-	58	200	-	250	-	300	ns
		$V_{CC} = 4.5\text{ V}$	-	21	40	-	50	-	60	ns
		$V_{CC} = 6.0\text{ V}$	-	17	34	-	43	-	51	ns
		Dn to Qn; see Figure 10								
		$V_{CC} = 2.0\text{ V}$	-	69	210	-	265	-	315	ns
		$V_{CC} = 4.5\text{ V}$	-	25	42	-	53	-	63	ns
		$V_{CC} = 6.0\text{ V}$	-	20	36	-	45	-	54	ns
		PL to TCU, PL to TCD; see Figure 13								
		$V_{CC} = 2.0\text{ V}$	-	80	290	-	365	-	435	ns
		$V_{CC} = 4.5\text{ V}$	-	29	58	-	73	-	87	ns
		$V_{CC} = 6.0\text{ V}$	-	23	49	-	62	-	74	ns
		MR to TCU, MR to TCD; see Figure 13								
		$V_{CC} = 2.0\text{ V}$	-	74	285	-	355	-	430	ns
		$V_{CC} = 4.5\text{ V}$	-	27	57	-	71	-	86	ns
		$V_{CC} = 6.0\text{ V}$	-	22	48	-	60	-	73	ns

Table 8. Dynamic characteristics type 74HC193 ...continued

Symbol	Parameter	Conditions	25 °C			–40 °C to +85 °C		–40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
t_{pd}	propagation delay	Dn to $\overline{TCU}$, Dn to $\overline{TCD}$; see Figure 13								
		$V_{CC} = 2.0\text{ V}$	-	80	290	-	365	-	435	ns
		$V_{CC} = 4.5\text{ V}$	-	29	58	-	73	-	87	ns
		$V_{CC} = 6.0\text{ V}$	-	23	49	-	62	-	74	ns
t_{THL}	HIGH to LOW output transition time	see Figure 11								
		$V_{CC} = 2.0\text{ V}$	-	19	75	-	95	-	110	ns
		$V_{CC} = 4.5\text{ V}$	-	7	15	-	19	-	22	ns
		$V_{CC} = 6.0\text{ V}$	-	6	13	-	16	-	19	ns
t_{TLH}	LOW to HIGH output transition time	see Figure 11								
		$V_{CC} = 2.0\text{ V}$	-	19	75	-	95	-	110	ns
		$V_{CC} = 4.5\text{ V}$	-	7	15	-	19	-	22	ns
		$V_{CC} = 6.0\text{ V}$	-	6	13	-	16	-	19	ns
t_w	pulse width	CPU, CPD (HIGH or LOW); see Figure 8								
		$V_{CC} = 2.0\text{ V}$	100	22	-	125	-	150	-	ns
		$V_{CC} = 4.5\text{ V}$	20	8	-	25	-	30	-	ns
		$V_{CC} = 6.0\text{ V}$	17	6	-	21	-	26	-	ns
		MR (HIGH); see Figure 11								
		$V_{CC} = 2.0\text{ V}$	100	25	-	125	-	150	-	ns
		$V_{CC} = 4.5\text{ V}$	20	9	-	25	-	30	-	ns
		$V_{CC} = 6.0\text{ V}$	17	7	-	21	-	26	-	ns
		$\overline{PL}$ (LOW); see Figure 10								
		$V_{CC} = 2.0\text{ V}$	100	19	-	125	-	150	-	ns
		$V_{CC} = 4.5\text{ V}$	20	7	-	25	-	30	-	ns
		$V_{CC} = 6.0\text{ V}$	17	6	-	21	-	26	-	ns
t_{rec}	recovery time	$\overline{PL}$ to CPU, CPD; see Figure 10								
		$V_{CC} = 2.0\text{ V}$	50	8	-	65	-	75	-	ns
		$V_{CC} = 4.5\text{ V}$	10	3	-	13	-	15	-	ns
		$V_{CC} = 6.0\text{ V}$	9	2	-	11	-	13	-	ns
		MR to CPU, CPD; see Figure 11								
		$V_{CC} = 2.0\text{ V}$	50	0	-	65	-	75	-	ns
		$V_{CC} = 4.5\text{ V}$	10	0	-	13	-	15	-	ns
		$V_{CC} = 6.0\text{ V}$	9	0	-	11	-	13	-	ns
t_{su}	set-up time	Dn to $\overline{PL}$; see Figure 12 ; note: CPU = CPD = HIGH								
		$V_{CC} = 2.0\text{ V}$	80	22	-	100	-	120	-	ns
		$V_{CC} = 4.5\text{ V}$	16	8	-	20	-	24	-	ns
		$V_{CC} = 6.0\text{ V}$	14	6	-	17	-	20	-	ns

Table 8. Dynamic characteristics type 74HC193 ...continued

Symbol	Parameter	Conditions	25 °C			–40 °C to +85 °C		–40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
t _h	hold time	Dn to $\overline{\text{PL}}$; see Figure 12								
		V _{CC} = 2.0 V	0	–14	-	0	-	0	-	ns
		V _{CC} = 4.5 V	0	–5	-	0	-	0	-	ns
		V _{CC} = 6.0 V	0	–4	-	0		0	-	ns
		CPU to CPD, CPD to CPU; see Figure 14								
		V _{CC} = 2.0 V	80	22	-	100	-	120	-	ns
		V _{CC} = 4.5 V	16	8	-	20	-	24	-	ns
		V _{CC} = 6.0 V	8	6	-	17	-	20	-	ns
f _{max}	maximum frequency	CPU, CPD; see Figure 8								
		V _{CC} = 2.0 V	4.0	13.5	-	3.2	-	2.6	-	MHz
		V _{CC} = 4.5 V	20	41	-	16	-	13	-	MHz
		V _{CC} = 6.0 V	24	49	-	19	-	15	-	MHz
C _{PD}	power dissipation capacitance	V _I = GND to V _{CC} ; [2] V _{CC} = 5 V; f _i = 1 MHz	-	24	-	-	-	-	-	pF

[1] t_{pd} is the same as t_{PHL} and t_{PLH}.

[2] C_{PD} is used to determine the dynamic power dissipation (P_D in μW):

$$P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \sum (C_L \times V_{CC}^2 \times f_o) \text{ where:}$$

f_i = input frequency in MHz;

f_o = output frequency in MHz;

C_L = output load capacitance in pF;

V_{CC} = supply voltage in V;

N = number of inputs switching;

$\sum (C_L \times V_{CC}^2 \times f_o)$ = sum of outputs.

Table 9. Dynamic characteristics type 74HCT193

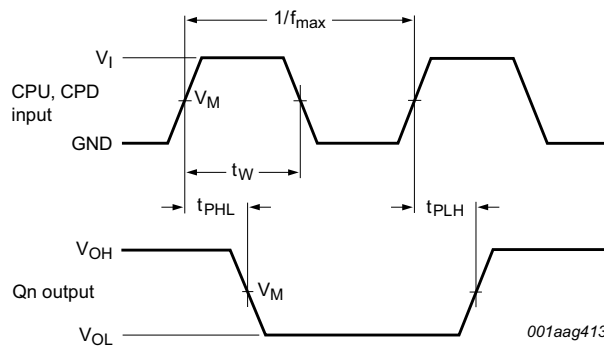
Symbol	Parameter	Conditions	25 °C			–40 °C to +85 °C		–40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
t_{pd}	propagation delay	CPU, CPD to Qn; see Figure 8 ^[1]								
		$V_{CC} = 4.5\text{ V}$	-	23	43	-	54	-	65	ns
		CPU to $\overline{TCU}$; see Figure 9								
		$V_{CC} = 4.5\text{ V}$	-	15	27	-	34	-	41	ns
		CPD to $\overline{TCD}$; see Figure 9								
		$V_{CC} = 4.5\text{ V}$	-	15	27	-	34	-	41	ns
		PL to Qn; see Figure 10								
		$V_{CC} = 4.5\text{ V}$	-	26	46	-	58	-	69	ns
		MR to Qn; see Figure 11								
		$V_{CC} = 4.5\text{ V}$	-	22	40	-	50	-	60	ns
		Dn to Qn; see Figure 10								
		$V_{CC} = 4.5\text{ V}$	-	27	46	-	58	-	69	ns
		PL to $\overline{TCU}$, PL to $\overline{TCD}$; see Figure 13								
		$V_{CC} = 4.5\text{ V}$	-	31	55	-	69	-	83	ns
		MR to $\overline{TCU}$, MR to $\overline{TCD}$; see Figure 13								
		$V_{CC} = 4.5\text{ V}$	-	29	55	-	69	-	83	ns
		Dn to $\overline{TCU}$, Dn to $\overline{TCD}$; see Figure 13								
		$V_{CC} = 4.5\text{ V}$	-	32	58	-	73	-	87	ns
t_{THL}	HIGH to LOW output transition time	see Figure 11								
		$V_{CC} = 4.5\text{ V}$	-	7	15	-	19	-	22	ns
t_{TLH}	LOW to HIGH output transition time	see Figure 11								
		$V_{CC} = 4.5\text{ V}$	-	7	15	-	19	-	22	ns
t_w	pulse width	CPU, CPD (HIGH or LOW); see Figure 8								
		$V_{CC} = 4.5\text{ V}$	25	11	-	31	-	38	-	ns
		MR (HIGH); see Figure 11								
		$V_{CC} = 4.5\text{ V}$	20	7	-	25	-	30	-	ns
		PL (LOW); see Figure 10								
		$V_{CC} = 4.5\text{ V}$	20	8	-	25	-	30	-	ns
t_{rec}	recovery time	$\overline{PL}$ to CPU, CPD; see Figure 10								
		$V_{CC} = 4.5\text{ V}$	10	2	-	13	-	15	-	ns
		MR to CPU, CPD; see Figure 11								
		$V_{CC} = 4.5\text{ V}$	10	0	-	13	-	15	-	ns

Table 9. Dynamic characteristics type 74HCT193 ...continued

Symbol	Parameter	Conditions	25 °C			–40 °C to +85 °C		–40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
t_{su}	set-up time	Dn to $\overline{PL}$; see Figure 12 ; note: CPU = CPD = HIGH								
		$V_{CC} = 4.5\text{ V}$	16	8	-	20	-	24	-	ns
t_h	hold time	Dn to $\overline{PL}$; see Figure 12								
		$V_{CC} = 4.5\text{ V}$	0	–6	-	0	-	0	-	ns
		CPU to CPD, CPD to CPU; see Figure 14								
		$V_{CC} = 4.5\text{ V}$	16	7	-	20	-	24	-	ns
f_{max}	maximum frequency	CPU, CPD; see Figure 8								
		$V_{CC} = 4.5\text{ V}$	20	43	-	16	-	13	-	MHz
C_{PD}	power dissipation capacitance	$V_I = \text{GND to } V_{CC} - 1.5\text{ V}$; [2] $V_{CC} = 5\text{ V}$; $f_i = 1\text{ MHz}$	-	26	-	-	-	-	-	pF

- [1] t_{pd} is the same as t_{PHL} and t_{PLH} .
- [2] C_{PD} is used to determine the dynamic power dissipation (P_D in μW):
 $P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \sum(C_L \times V_{CC}^2 \times f_o)$ where:
 f_i = input frequency in MHz;
 f_o = output frequency in MHz;
 C_L = output load capacitance in pF;
 V_{CC} = supply voltage in V;
 N = number of inputs switching;
 $\sum(C_L \times V_{CC}^2 \times f_o)$ = sum of outputs.

11. Waveforms

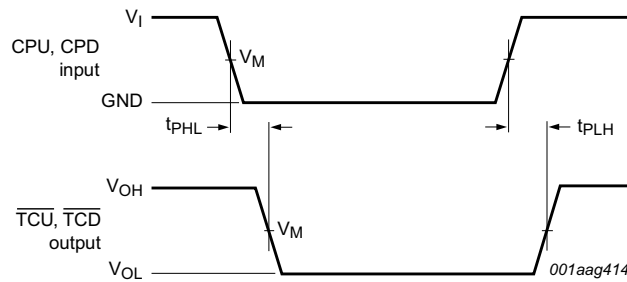


Measurement points are given in [Table 10](#).

t_{PLH} and t_{PHL} are the same as t_{pd} .

Logic levels V_{OL} and V_{OH} are typical output voltage levels that occur with the output load.

Fig 8. The clock (CPU, CPD) to output (Qn) propagation delays, the clock pulse width, and the maximum clock pulse frequency

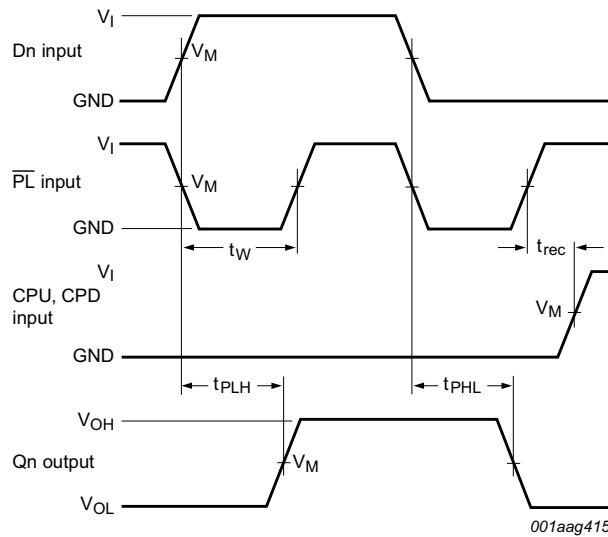


Measurement points are given in [Table 10](#).

t_{PLH} and t_{PHL} are the same as t_{pd} .

Logic levels V_{OL} and V_{OH} are typical output voltage levels that occur with the output load.

Fig 9. The clock (CPU, CPD) to terminal count output ($\overline{TCU}$, $\overline{TCD}$) propagation delays

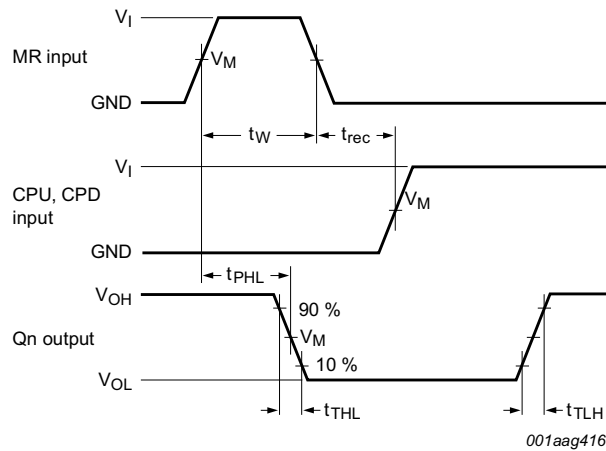


Measurement points are given in [Table 10](#).

t_{PLH} and t_{PHL} are the same as t_{pd} .

Logic levels V_{OL} and V_{OH} are typical output voltage levels that occur with the output load.

Fig 10. The parallel load input ($\overline{PL}$) and data (Dn) to Qn output propagation delays and $\overline{PL}$ removal time to clock input (CPU, CPD)

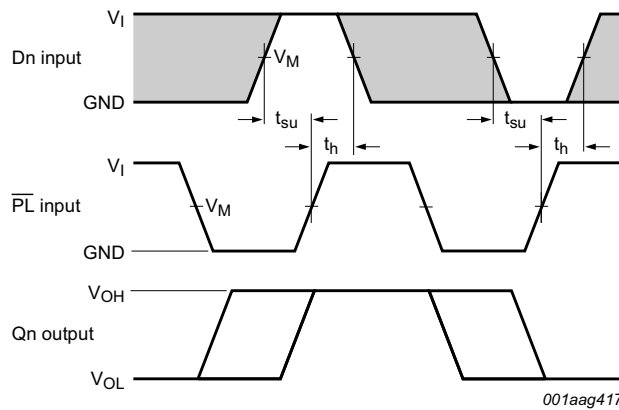


Measurement points are given in [Table 10](#).

t_{PLH} and t_{PHL} are the same as t_{pd} .

Logic levels V_{OL} and V_{OH} are typical output voltage levels that occur with the output load.

Fig 11. The master reset input (MR) pulse width, MR to Qn propagation delays, MR to CPU, CPD removal time and output transition times

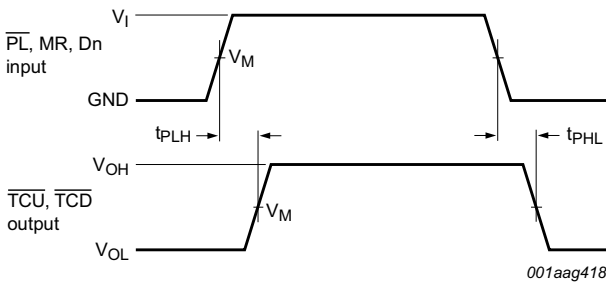


The shaded areas indicate when the input is permitted to change for predictable output performance.

Measurement points are given in [Table 10](#).

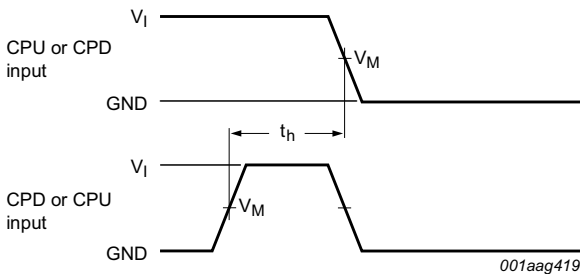
Logic levels V_{OL} and V_{OH} are typical output voltage levels that occur with the output load.

Fig 12. The data input (Dn) to parallel load input (PL) set-up and hold times



Measurement points are given in [Table 10](#).
 t_{PLH} and t_{PHL} are the same as t_{pd} .
Logic levels V_{OL} and V_{OH} are typical output voltage levels that occur with the output load.

Fig 13. The data input (Dn), parallel load input ($\overline{\text{PL}}$) and the master reset input (MR) to the terminal count outputs ($\overline{\text{TCU}}$, $\overline{\text{TCD}}$) propagation delays



Measurement points are given in [Table 10](#).

Fig 14. The CPU to CPD or CPD to CPU hold times

Table 10. Measurement points

Type	Input		Output
	V_M	V_I	V_M
74HC193	$0.5 \times V_{CC}$	GND to V_{CC}	$0.5 \times V_{CC}$
74HCT193	1.3 V	GND to 3 V	1.3 V

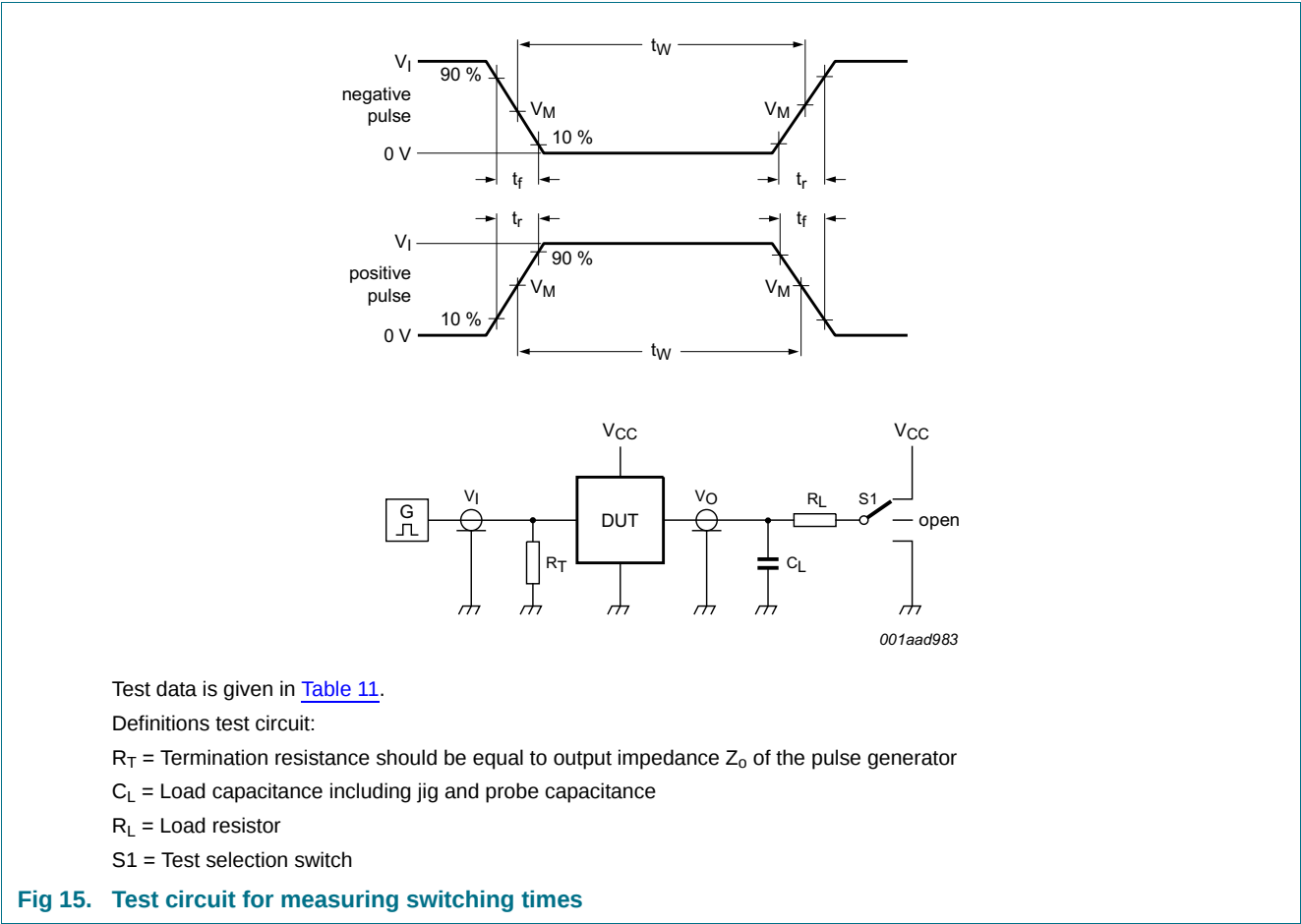


Table 11. Test data

Type	Input		Load		S1 position
	V_I	t_r, t_f	C_L	R_L	t_{PHL}, t_{PLH}
74HC193	V_{CC}	6 ns	15 pF, 50 pF	1 k Ω	open
74HCT193	3 V	6 ns	15 pF, 50 pF	1 k Ω	open

12. Application information

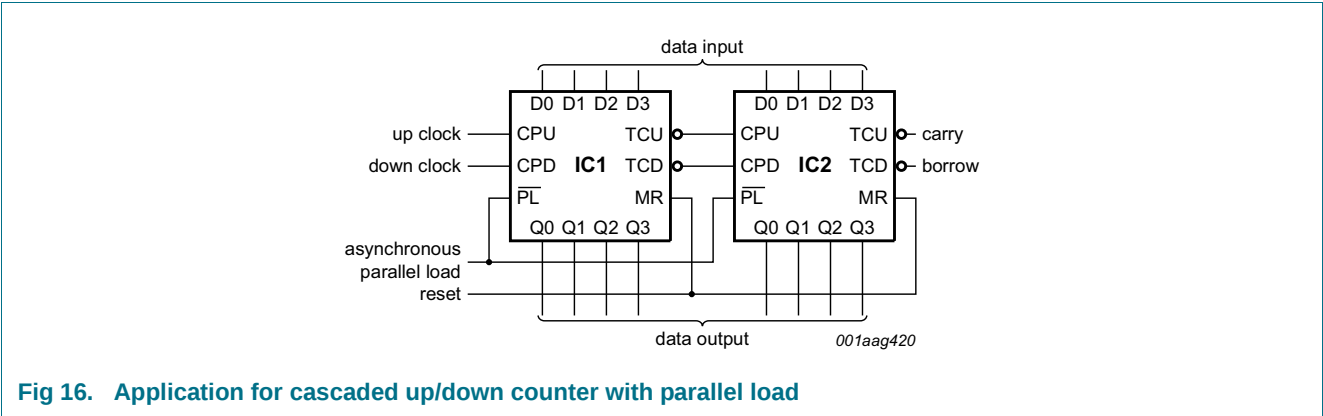


Fig 16. Application for cascaded up/down counter with parallel load

13. Package outline

SO16: plastic small outline package; 16 leads; body width 3.9 mm

SOT109-1

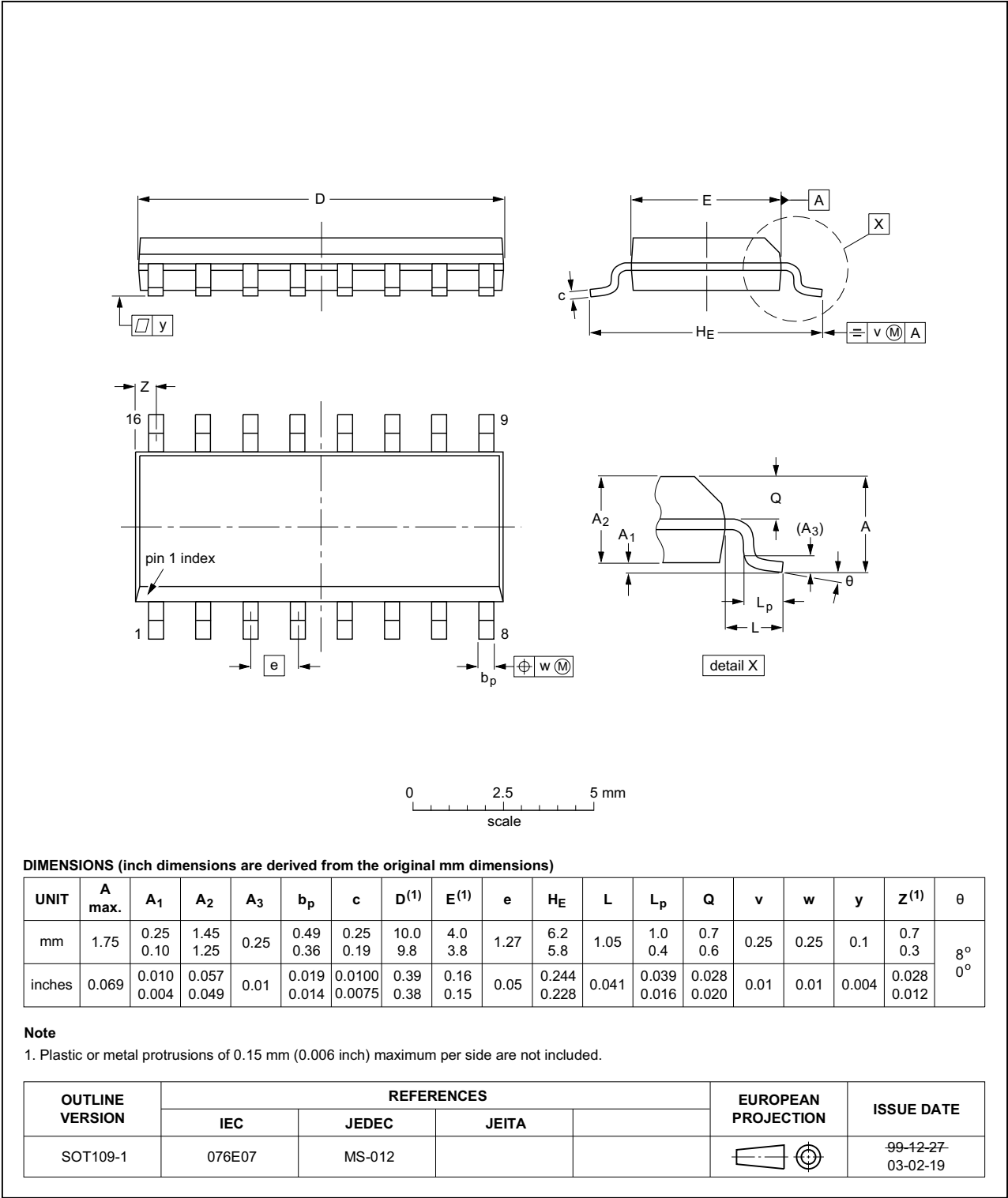


Fig 17. Package outline SOT109-1 (SO16)

SSOP16: plastic shrink small outline package; 16 leads; body width 5.3 mm

SOT338-1

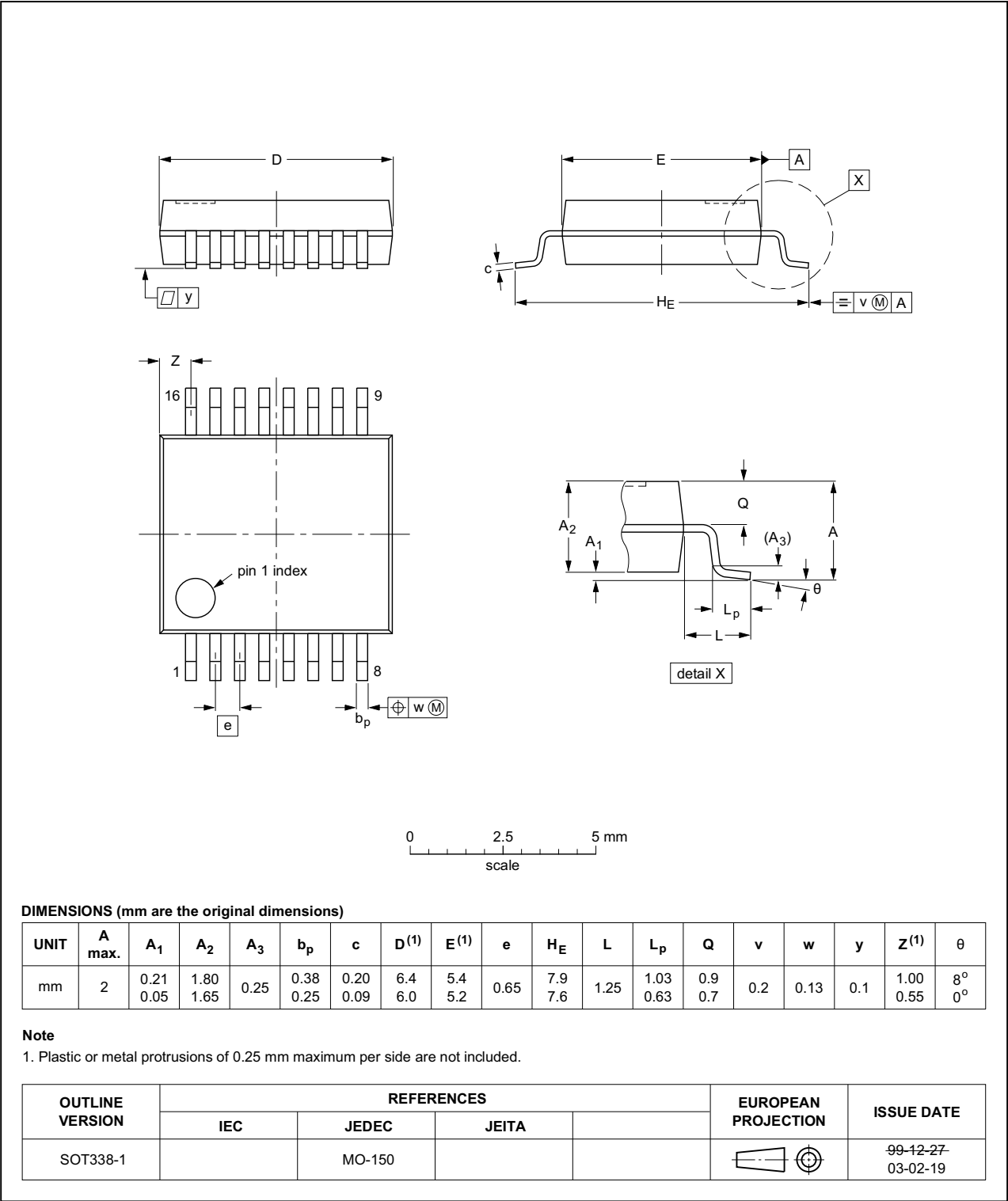


Fig 18. Package outline SOT338-1 (SSOP16)

TSSOP16: plastic thin shrink small outline package; 16 leads; body width 4.4 mm

SOT403-1

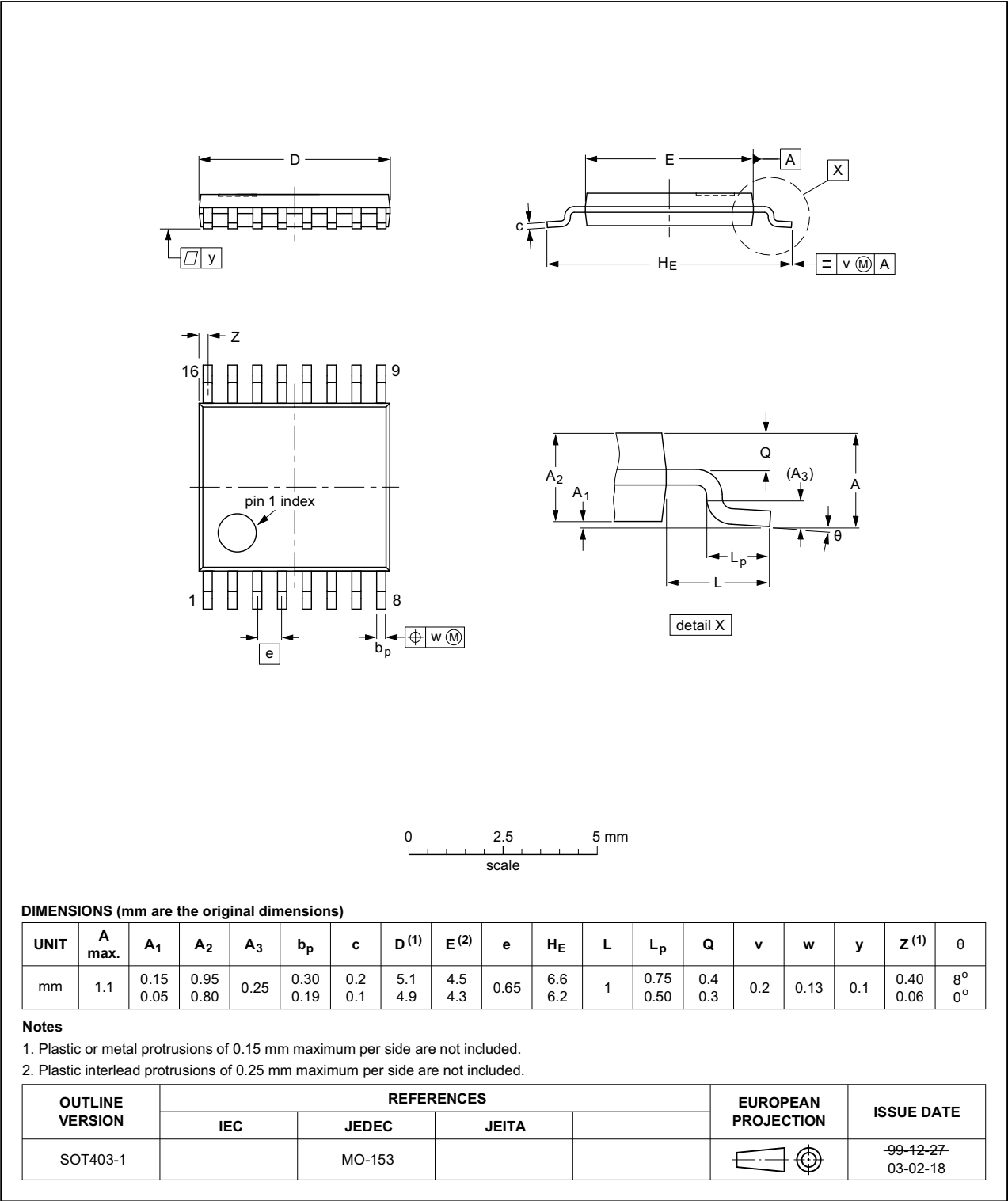


Fig 19. Package outline SOT403-1 (TSSOP16)

14. Abbreviations

Table 12. Abbreviations

Acronym	Description
CMOS	Complementary Metal-Oxide Semiconductor
DUT	Device Under Test
ESD	ElectroStatic Discharge
HBM	Human Body Model
MM	Machine Model
TTL	Transistor-Transistor Logic

15. Revision history

Table 13. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74HC_HCT193 v.5	20160129	Product data sheet	-	74HC_HCT193 v.4
Modifications:	• Type numbers 74HC193N and 74HCT193N (SOT38-4) removed.			
74HC_HCT193 v.4	20130624	Product data sheet	-	74HC_HCT193 v.3
Modifications:	• General description updated.			
74HC_HCT193 v.3	20070523	Product data sheet	-	74HC_HCT193_CNV v.2
Modifications:	• The format of this data sheet has been redesigned to comply with the new identity guidelines of NXP Semiconductors. • Legal texts have been adapted to the new company name where appropriate. • Family specification included			
74HC_HCT193_CNV v.2	19970828	Product specification	-	-

16. Legal information

16.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <http://www.nxp.com>.

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